



2N7002W

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
60V	7.5Ω @ V _{GS} = 5V	115mA

Features and Benefits

- Low-On Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

 $\underline{https://www.diodes.com/products/automotive/automotive-products/.}$

 This part is qualified to JEDEC standards (as references in AEC-Q101) for High Reliability.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Power Management Functions

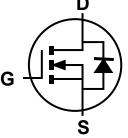
Mechanical Data

- Case: SOT-323 (Standard)
- Case Material: Molded Plastic, "Green" Molding Compound,
 Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42
 leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

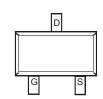
SOT-323 (Standard)



Top View



Equivalent Circuit



Top View

Ordering Information (Note 4)

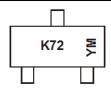
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	Part Number	Case	Packaging
	2N7002W-7-F	SOT-323 (Standard)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



K72 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: I = 2021) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2012		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Z		ı	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteris	stic	Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		V_{DGR}	60	V
Gain-Source Voltage	Continuous Pulsed (Note 7)	V_{GSS}	±20 ±40	V
Drain Current (Note 5)	Continuous Continuous @ +100°C Pulsed	I _D	115 73 800	mA

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

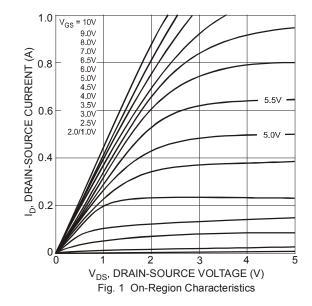
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	В	200	mW
Derating above T _A = +25°C	PD	1.60	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

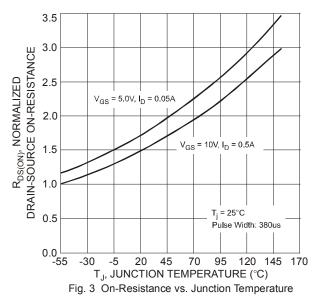
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _J = +25°C @ T _J = +125°C	I _{DSS}	_		1.0 500	μА	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage		V _{GS(th)}	1.0		2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = +25°C	D		1.8	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
Static Dialii-Source Off-Resistance	@ T _J = +125°C	R _{DS(on)}	_	2.6	13.5	12	$V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		$I_{D(on)}$	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		g FS	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance		C _{iss}	_	22	50	pF	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Output Capacitance Reverse Transfer Capacitance		Coss	_	11	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
		C _{rss}	_	2.0	5.0	pF	1 - 1.000112
Turn-On Delay Time	•	t _{D(on)}	_	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(off)}	_	11	20	ns	R_L = 150 Ω , V_{GEN} = 10 V , R_{GEN} = 25 Ω

5. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout, which can be found on our website at www.diodes.com/package-outlines.html. 6. Short duration pulse test used to minimize self-heating effect. 7. Guaranteed by design. Not subject to production testing. Notes:







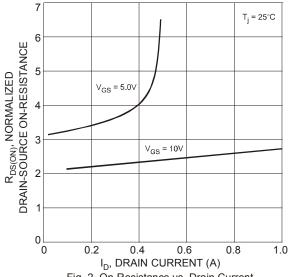
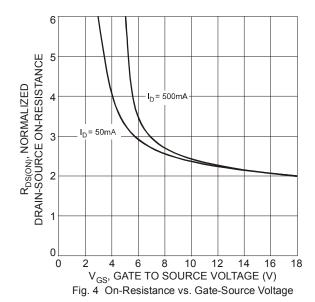


Fig. 2 On-Resistance vs. Drain Current

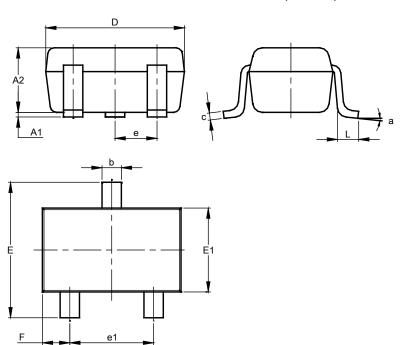




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323 (Standard)

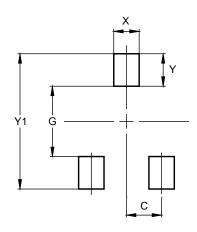


SOT323 (Standard)							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.80	1.00	0.90				
b	0.20	0.40	0.30				
С	0.08	0.18	0.13				
D	1.80	2.20	2.00				
Е	2.00	2.45	2.225				
E1	1.15	1.35	1.25				
е			0.65				
e1	1.20	1.40	1.30				
F	0.25	0.475	0.3625				
L	0.25	0.46	0.355				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$

SOT323 (Standard)



Dimensions	Value (in mm)		
С	0.650		
G	1.300		
Х	0.470		
Υ	0.600		
Y1	2.500		



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